# Diels-Alder addition of some 6- and 5-member ring aromatic compounds on the Si(001)-2×1 surface: dependence of the binding energy on the resonance energy of the aromatic compounds

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Abstract An energy decomposition scheme is proposed for understanding of the relative low binding energy of the [4+2] cycloaddition of benzene on the Si(001)-2×1 surface. By means of density functional cluster model calculations, this scheme is demonstrated to be applicable to some other 6- and 5-member ring aromatic compounds, giving a trend that the binding energy of the [4+2] cycloaddition products of those aromatic compounds on the Si(001) surface depends strongly on their resonance energy.

Keywords: silicon, aromatic compound, adsorption, Diels-Alder reaction, cluster model, density functional theory.

The interaction of  $\pi$ -conjugated aromatic compounds with silicon surfaces is not only of fundamental interest, but also of practical importance to the development of highly ordered thin-film of conducting polymers<sup>[1,2]</sup>. Growing efforts devoted to this topic include the experimental studies of the adsorption of benzene  $(C_6H_6)^{[3]}$ , pyridine  $(C_5H_5N)^{[4]}$ , furan  $(C_4H_4O)^{[5,6]}$ , thiophene  $(C_4H_4S)^{[5,7]}$  and pyrrole<sup>[5]</sup> on the Si(111) surface and the adsorption of benzene  $^{[8-10]}$  and pyrrole<sup>[11]</sup> on the Si(001)-2×1 surface, as well as the theoretical studies of benzene adsorption on the Si(001)-2×1 surface<sup>[12-15]</sup>. Of particular interest is that recent experimental and theoretical studies revealed the occurrence of [4+2] cycloaddition (Diels-Alder reaction) of benzene onto the weakly  $\pi$ -bonded Si-Si dimer of the Si(001)-2×1 surface and that the binding energy of the thus-formed di- $\sigma$  bonded, butterfly-like adspecies is far lower than that of the analogous reaction of simple dienes (e.g., 1,3-cyclohexadiene  $(C_6H_8)$ ) on the same surface<sup>[8,12-15]</sup>. This intriguing phenomenon can be ascribed to the aromatic stabilization in benzene<sup>[12]</sup>. For a better understanding of this intriguing phenomenon, a simple energy decomposition scheme (see scheme 1(1)), which correlates the binding energy of the [4+2] cycloaddition product with the resonance energy ( $E_R$ ) of benzene, is proposed in this paper. We will show that this simple scheme is applicable to

other 6- and 5-member ring aromatic compounds and that the binding energy of the corresponding [4+2] cycloaddition products on the Si(001)-2×1 surface displays strong dependence on the resonance energy of the aromatic compounds.

$$\begin{array}{c|c}
 & \Delta E_1 \\
X & Cocalization X
\end{array}$$

$$\begin{array}{c|c}
 & \Delta E_2 \\
\hline
Si(001)
\end{array}$$

$$\begin{array}{c|c}
 & Si \\
\hline
Si
\end{array}$$

$$\begin{array}{c|c}
 & Si
\end{array}$$

$$\underbrace{\sum_{\substack{X \text{ Localization} \\ E_b}}^{\Delta E_1} \underbrace{\sum_{\substack{Si(001)}}^{\Delta E_2}}_{Si(001)}}_{E_b}$$

$$\underbrace{\sum_{\substack{Si \in Si}}^{X}}_{Si}$$
(2)

Scheme 1. Energy decomposition schemes for the adsorption of 6- and 5-member ring aromatic compounds on a Si-Si dimer site of the Si(001)-2×1 surface.

# 1 Energy decomposition scheme

In scheme 1(1), the [4+2] cycloaddition process is divided into two ideal steps. First, the  $\pi$ -conjugated benzene is ideally localized into a nonaromatic analog, i.e., 1,3,5-cyclohexatriene. The energy cost ( $\Delta E_1$ ) in this step should correspond to the so-called resonance energy ( $E_R$ )<sup>[16]</sup> of benzene. Second, the nonaromatic analog undergoes [4+2] cycloaddition onto a Si-Si dimer. This step is exothermic with a reaction heat ( $\Delta E_2$ ) close to the heat of the analogous reaction of 1,3-cyclohexadiene on the same surface site. Therefore, the difference in binding energy between the [4+2] cycloaddition products of benzene and 1,3-cyclohexadiene should have a value close to the difference in  $E_R$  between benzene and 1,3-cyclohexadiene. This is indeed the case, as previous B3LYP/6-31G\*\* cluster model calculations<sup>[12]</sup> did predict a difference of 136.3 kJ/mol in binding energy between benzene and 1,3-cyclohexadiene, which is comparable to the difference ( $\sim$ 118.3 kJ/mol)<sup>[16]</sup> in  $E_R$  between benzene and 1,3-cyclohexadiene.

Scheme 1(1) can be generalized to the cases of other 6-member ring aromatic compounds containing one (or more) heteroatom(s) and to those of the 5-member ring aromatic compounds depicted in scheme 1(2). For example, for a series of 6-member ring compounds listed in scheme 1(1), their nonaromatic analogs contain the same localized dienes as the 1,3-cyclohexadiene has and would have similar values of  $\Delta E_2$  when undergoing [4+2] addition on the Si(001) surface. Note that among them, benzene has the largest value of  $E_R$ . It is thus deducible that the [4+2] cycloaddition reactions of the heterocyclic ones would be more exothermic than that of benzene and would follow such a trend that the compound having higher  $E_R$  would give lower binding energy. A similar trend could also be expected for the 5-member ring compounds listed in scheme 1(2). To confirm the above inference, we have performed density functional cluster model calculations to explore the energetics of the [4+2] cycloaddition of five 6-member ring compounds, including benzene, pyridine, silabenzene ( $C_5H_6Si$ ), phosphabenzene ( $C_5H_5P$ ), pyrazine ( $C_4H_4N_2$ )

and 1,3-cyclohexadiene, and four 5-member ring compounds, including pyrrole, thiophene, furan and cyclopentadiene ( $C_5H_6$ ), onto a Si-Si dimer site of the Si(001)-2×1 surface.

## 2 Computational model and method

We used a  $Si_9H_{12}$  cluster<sup>[12,15]</sup> to model the Si-Si dimer site on the reconstructed Si(001)-2×1surface. The hybrid B3LYP density functional method<sup>[17,18]</sup> and the standard 6-31G\* basis set were employed in our calculations. Adsorption geometries were optimized at the B3LYP/6-31G\* level of theory with no geometric constraint. Binding energy was calculated at the same level of theory without zero-point energy (ZPE) correction. All calculations were performed using the Gaussian98 program<sup>[19]</sup>.

Table 1	Key structural and energetic parameters for the products of [4+2] cycloaddition of some 6- or 5-member ring aromatic
	compounds on the Si(001)-2×1 surface (predicted at the B3LYP/6-31G* level)

	6-member ring						5-member ring			
·	C <sub>6</sub> H <sub>6</sub>	C₅H₅P	C <sub>5</sub> H <sub>5</sub> N	C <sub>5</sub> H <sub>6</sub> Si	C <sub>4</sub> H <sub>4</sub> N <sub>2</sub>	C <sub>6</sub> H <sub>8</sub>	C <sub>4</sub> H <sub>5</sub> N	C <sub>4</sub> H <sub>4</sub> S	C <sub>4</sub> H <sub>4</sub> O	C <sub>5</sub> H <sub>6</sub>
C-Si/nm	0.1976	0.1979	0.1977	0.1978	0.1965	0.1953	0.2010	0.1965	0.1993	0.1965
	0.1976	$0.1954^{a)}$	0.1973 <sup>a)</sup>	$0.1958^{a)}$	0.1965	0.1953				
Si-Si-C/(°)	96.2	97.2	95.6	98.3	94.8	96.6	89.2	92.5	88.5	90.4
	96.2	98.3 <sup>a)</sup>	95.3a)	99.9a)	94.8	96.6				
$E_{b}/kJ \cdot mol^{-1b}$	-91.1	-121.2	-106.6	-109.9	-123.7	-234.9	-105.3	-150.5	-128.7	-217.4
$E_{R}/kJ \cdot mol^{-1[16]}$	118.3	108.7	107.0	105.8	94.9	0.0	94.1	69.0	50.6	0.0
$\Delta E_2/\text{kJ} \cdot \text{mol}^{-1c}$	-209.4	-229.9	-213.6	-215.7	-218.6	-234.9	-199.4	-219.5	-179.3	-217.4

a) Parameters relevant to the carbon atom neighboring to the heteroatom; b)  $E_b = E(\text{adsorbate}/C_9H_{12}) - E(\text{adsorbate}) - E(C_9H_{12})$ ; c)  $\Delta E_2 = E_b - E_R$ .

# 3 Results and discussion

The B3LYP-calculated key structural and energetic parameters for the [4+2] addition products of those 6- and 5-member ring compounds on the Si-Si dimer sites are listed in table 1, together with the theoretical resonance energy reported by Dewar et al. <sup>[16]</sup> and the values of  $\Delta E_2$  estimated with the formulae  $\Delta E_2 = E_b - E_R$ . Our B3LYP/6-31G\* calculations reveal that:

- (i) The [4+2] cycloaddition process on the Si(001)-2×1 surface is exothermic for all the 6and 5-member ring compounds concerned. The products are di-σ bonded adspecies with the thus-formed Si-C bond lengths ranging within 0.195—0.201 nm.
- (ii) The nonaromatic ones, i.e., 1,3-cyclohexadiene and cyclopentadiene, give the largest binding energy, whereas the most aromatic ones, benzene and pyrrole, give the smallest binding energy in the 6- and 5-member ring compounds, respectively.
- (iii) The calculated binding energy for the 6-member ring compounds gives the following order of magnitude:  $C_6H_8$  (-234.9 kJ/mol) >  $C_4H_4N_2$  (-123.7 kJ/mol) >  $C_5H_5P$  (-121.2 kJ/mol) >  $C_5H_6Si$  (-109.9 kJ/mol) >  $C_5H_5N$  (-106.6 kJ/mol) >  $C_6H_6$  (-91.1 kJ/mol). Taking  $C_5H_5P$  as an exception, we found that this is the reverse order of their  $E_R$  values. That is, the higher  $E_R$  the compound has, the lower the binding energy given in the Diels-Alder addition-like adsorption on

the Si(001)-2×1 surface is. A similar trend was also found for the 5-member ring compounds, and expected that the more aromatic thiophene gives larger binding energy than the less aromatic furan does.

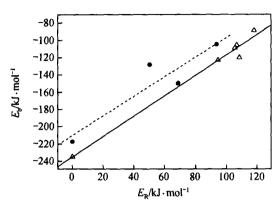


Fig. 1. Calculated binding energy  $(E_b)$  for the [4+2] cycloaddition of some 6- and 5-member ring compounds on the Si(001) surface as a function of the resonance energy  $(E_R)$  of these compounds. Further linear fitting gives the solid line and dashed line for 6- and 5-member ring compounds, respectively.  $\triangle$ , 6-member ring;  $\bigcirc$ , 5-member ring.

The calculated binding energy was further plotted as a function of the corresponding resonance energy reported by Dewar et al. [16], as depicted in fig. 1. The correlation equations,  $E_b = 1.171 \times E_R - 235.4$  for the 6-member ring compounds and  $E_b = 1.124 \times E_R - 210.5$  for the 5-member ring compounds, obtained by linear fitting demonstrate the nearly linear dependence of the binding energy of the [4+2] cycloaddition adspecies on the resonance energy of those compounds. The appreciable deviations at phosphabenzene for the 6-member ring compounds, and at furan

and thiophene for the 5-member ring compounds might be a reflection of either the rather different ring strains of those compounds from those of other compounds of the same lines or the imperfectness of the  $E_R$  values reported<sup>[16]</sup>. Note that the determination of  $E_R$  is a subject of long-term controversy<sup>[16]</sup>.

In summary, we have proposed an energy decomposition scheme for the understanding of the relative low binding energy of the [4+2] cycloaddition of benzene on the Si(001)-2×1 surface. By means of density functional cluster model calculations, we demonstrate that this scheme is applicable to some other 6- and 5-member ring aromatic compounds and the binding energy of the [4+2] cycloaddition products of those aromatic compounds on the Si(001) surface depends strongly on their resonance energy. We should note that other bonding configurations of those 6- and 5-member ring compounds on the Si(001)-2×1 surface, e.g., the di-σ bonding configurations involving direct heteroatom-surface bond and the tetra-σ bonding configurations, have also been considered in our calculations. The results will be published elsewhere. Needless to say, the energy decomposition scheme proposed for the Diels-Alder addition-like surface reaction is also applicable to the normal Diels-Alder reactions between aromatic compounds and alkenes.

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